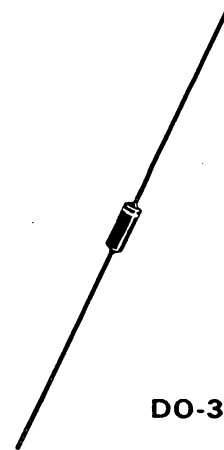




1N821, A, 1N823, A (SILICON)
1N825, A, 1N827, A
1N829, A

Temperature-compensated zener reference diodes



DO-35

MAXIMUM RATINGS

- Junction Temperature: -55 to +175°C
- Storage Temperature: -65 to +175°C
- DC Power Dissipation: 400 mW @ T_A = 50°C

MECHANICAL CHARACTERISTICS

- CASE: Hermetically sealed, all-glass
- DIMENSIONS: See outline drawing.
- FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
- POLARITY: Cathode indicated by polarity band.

MOUNTING POSITION: Any

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

JEDEC Type No.	Maximum Voltage Change ΔV _Z (Volts)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C	Maximum Dynamic Impedance Z _{ZT} Ohms
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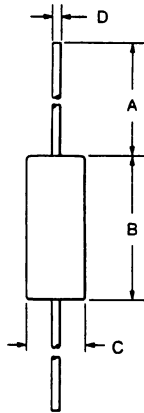
V_Z = 6.2 V ±5.0% * @ I_{ZT} = 7.5 mA

1N821	0.096	-55, 0, +25, +75, +100 ↓	0.01	15 ↓
1N823	0.048		0.005	
1N825	0.019		0.002	
1N827	0.009		0.001	
1N829	0.005		0.0005	
1N821A	0.096		0.01	10 ↓
1N823A	0.048		0.005	
1N825A	0.019		0.002	
1N827A	0.009		0.001	
1N829A	0.005		0.0005	

CAPACITANCE (C) = 30 to 400 pF @ 90% of V_Z
FORWARD BREAKDOWN VOLTAGE (V_F) = 15 to 400 V

PHYSICAL DIMENSIONS

JEDEC DO-35 outline



DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.0			25.40		
B			.180			4.57
C			.075			1.91
D		.020		0.508		